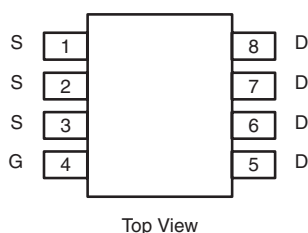


N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
30	0.0115 at $V_{GS} = 10$ V	16	13.3 nC
	0.016 at $V_{GS} = 4.5$ V	12.7	

SCHOTTKY AND BODY DIODE PRODUCT SUMMARY		
V_{DS} (V)	V_{SD} (V) Diode Forward Voltage	I_S (A)
30	0.4 at 2 A	5 ^a

SO-8



Ordering Information: Si4396DY-T1-E3 (Lead (Pb)-free)
Si4396DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

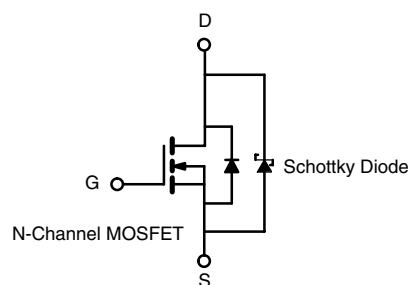
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested

APPLICATIONS

- Notebook Logic DC/DC
- Low Side



RoHS
COMPLIANT
HALOGEN
FREE
Available



ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	I_D	16	A
	$T_C = 70$ °C		12.7	
	$T_A = 25$ °C		12.3 ^{b, c}	
	$T_A = 70$ °C		9.7 ^{b, c}	
Pulsed Drain Current		I_{DM}	40	
Continuous Source-Drain Diode Current	$T_C = 25$ °C	I_S	5	
	$T_A = 25$ °C		2.8 ^{b, c}	
Single Pulse Avalanche Current		I_{AS}	20	mJ
Single Pulse Avalanche Energy		E_{AS}	20	
Maximum Power Dissipation	$T_C = 25$ °C	P_D	5.4	W
	$T_C = 70$ °C		3.4	
	$T_A = 25$ °C		3.1 ^{b, c}	
	$T_A = 70$ °C		2.0 ^{b, c}	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient ^{b, d}	$t \leq 10$ s	R_{thJA}	34	40	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	23	

Notes:

- a. Based on $T_C = 25$ °C.
b. Surface Mounted on 1" x 1" FR4 board.
c. $t = 10$ s.
d. Maximum under Steady State conditions is 85 °C/W.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30			V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.2		2.6	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V		0.18	1	mA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 100 °C		22	100	
On -State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	20			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A		0.0095	0.0115	Ω
		V _{GS} = 4.5 V, I _D = 8 A		0.0132	0.0160	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 10 A		40		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		1675		pF
Output Capacitance	C _{oss}			410		
Reverse Transfer Capacitance	C _{rss}			150		
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 10 A		29.6	45	nC
Gate-Source Charge	Q _{gs}	V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 10 A		13.3	20	
Gate-Drain Charge	Q _{gd}			4.5		
Gate Resistance	R _g			4.3		
Gate Resistance	R _g	f = 1 MHz		1.55	2.4	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 3 Ω I _D ≅ 5 A, V _{GEN} = 4.5 V, R _g = 1 Ω		22	33	ns
Rise Time	t _r			71	110	
Turn-Off Delay Time	t _{d(off)}			22	33	
Fall Time	t _f			7	14	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 3 Ω I _D ≅ 5 A, V _{GEN} = 10 V, R _g = 1 Ω		11	18	
Rise Time	t _r			29	45	
Turn-Off Delay Time	t _{d(off)}			24	36	
Fall Time	t _f			8	15	
Drain-Source Body Diode and Schottky Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			5	A
Pulse Diode Forward Current ^a	I _{SM}				40	
Body Diode Voltage	V _{SD}	I _S = 2 A		0.35	0.4	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 4 A, dI/dt = 100 A/μs, T _J = 25 °C		29	45	ns
Body Diode Reverse Recovery Charge	Q _{rr}			18	27	nC
Reverse Recovery Fall Time	t _a			14		ns
Reverse Recovery Rise Time	t _b			15		

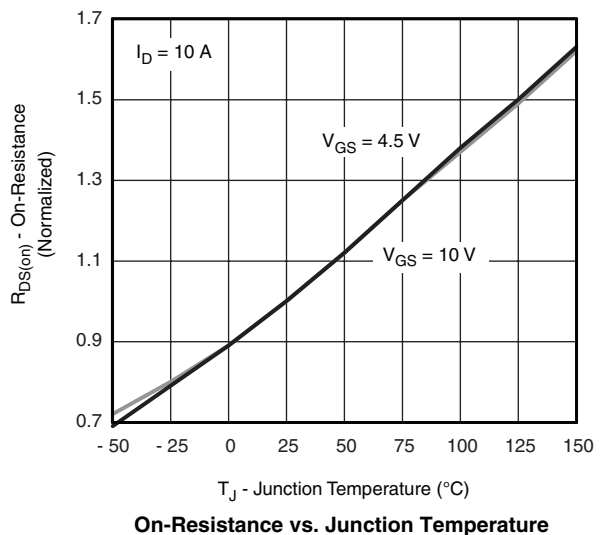
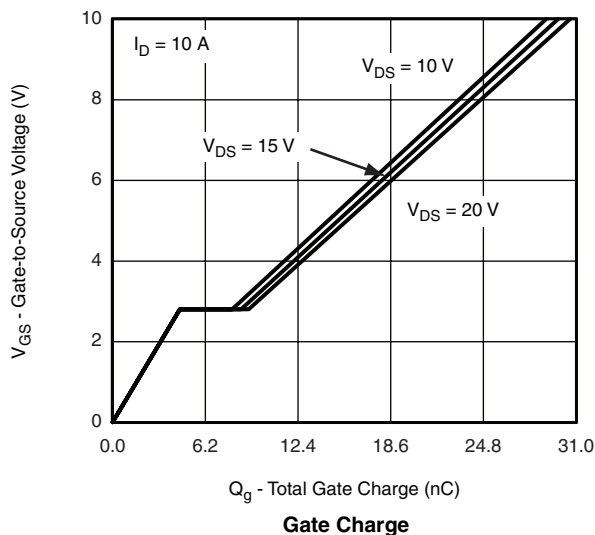
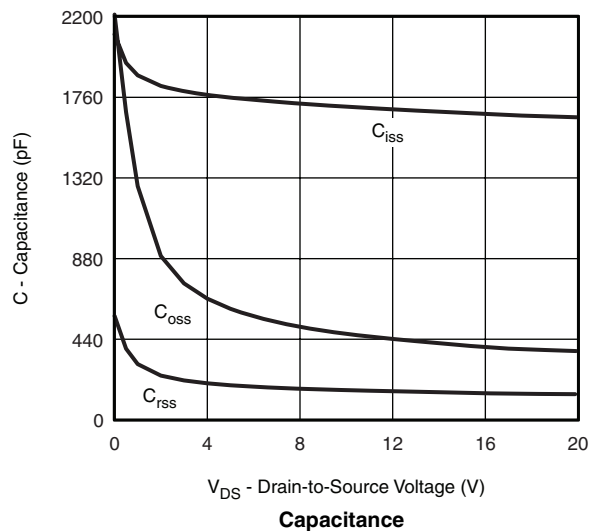
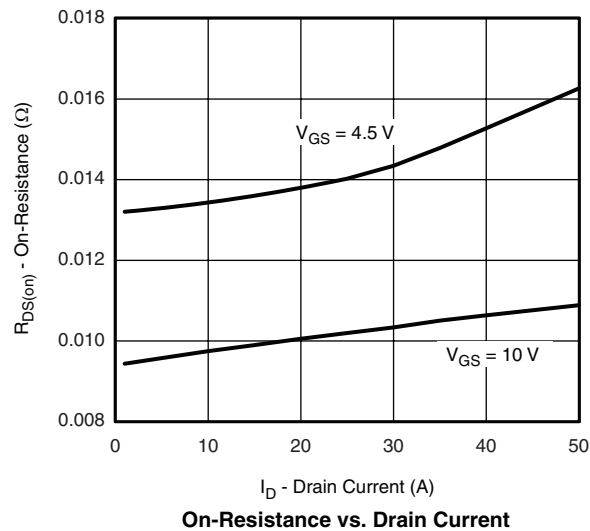
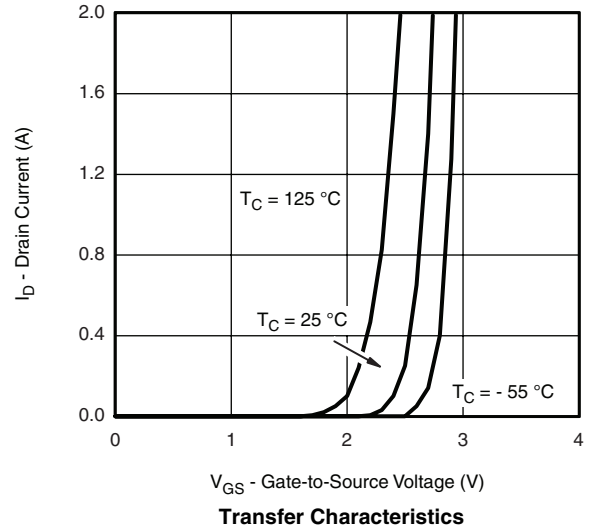
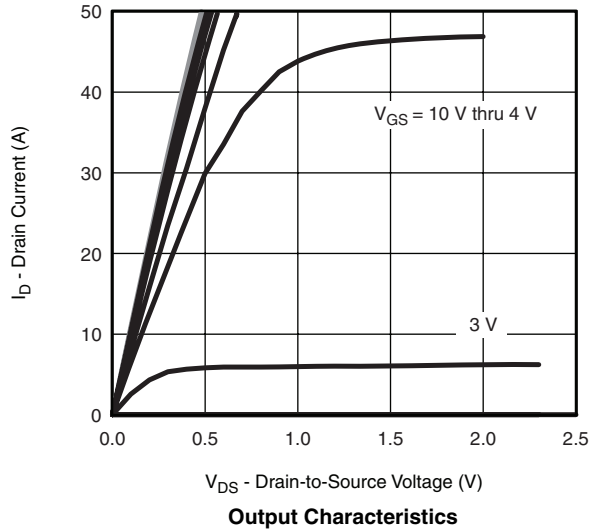
Notes:

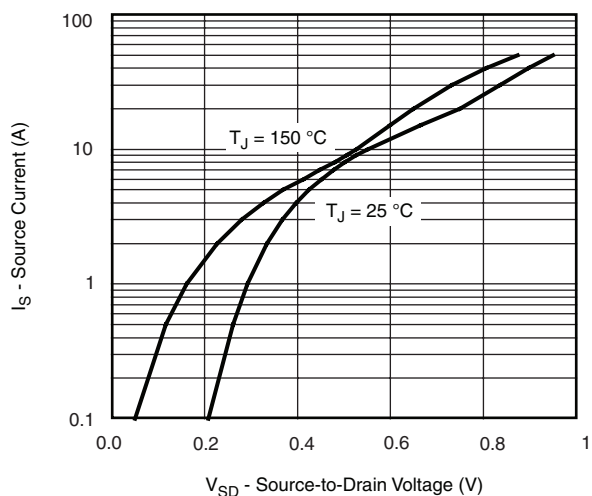
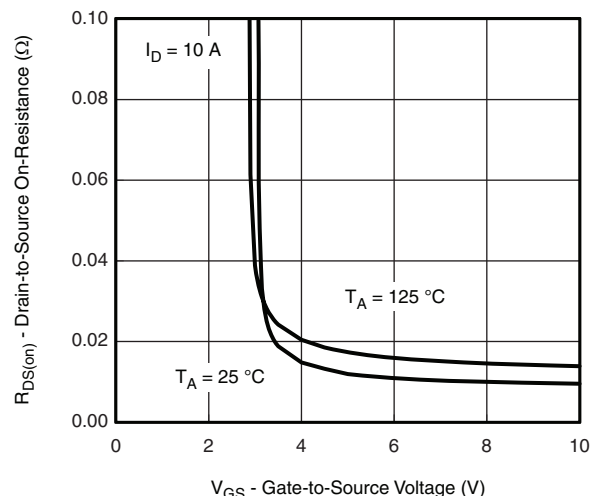
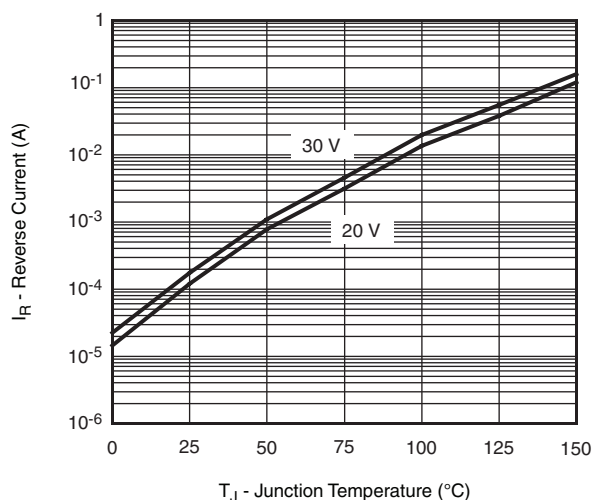
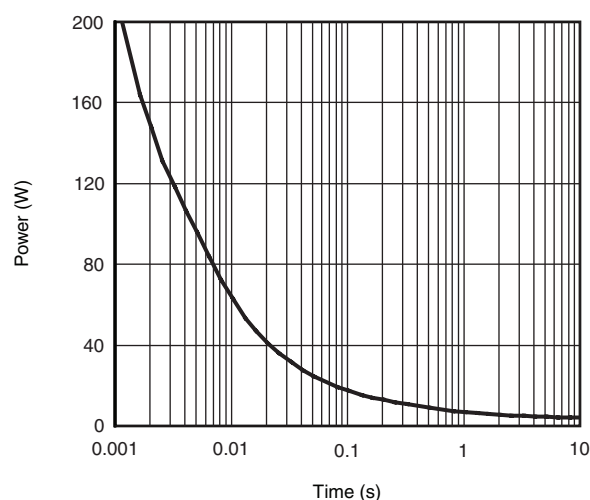
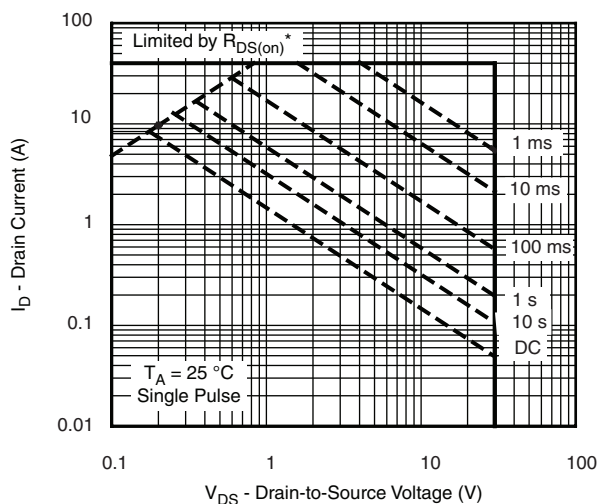
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

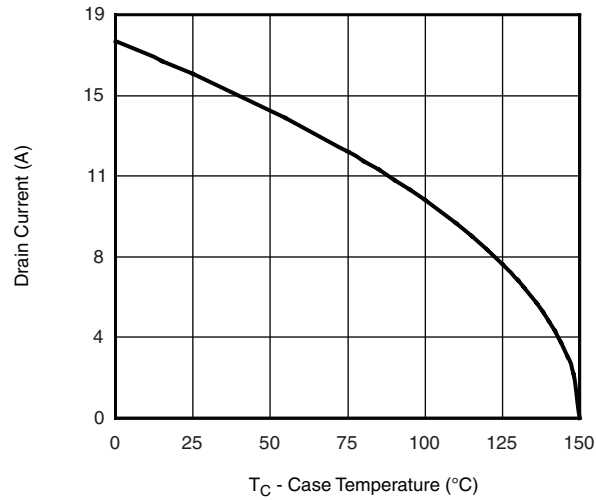
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

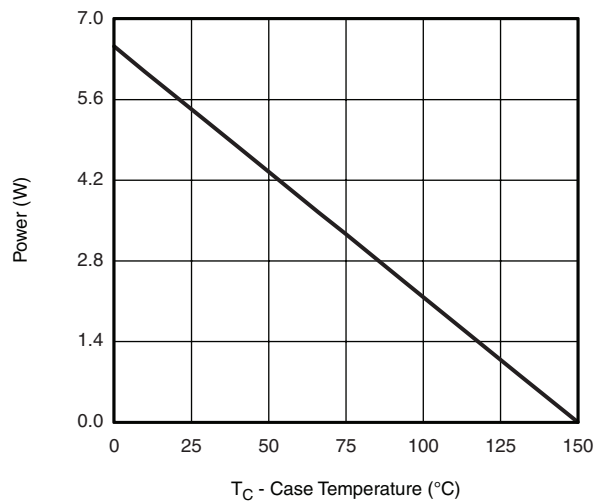


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Reverse Current (Schottky)****Junction-to-Ambient****Safe Operating Area*** $V_{DS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

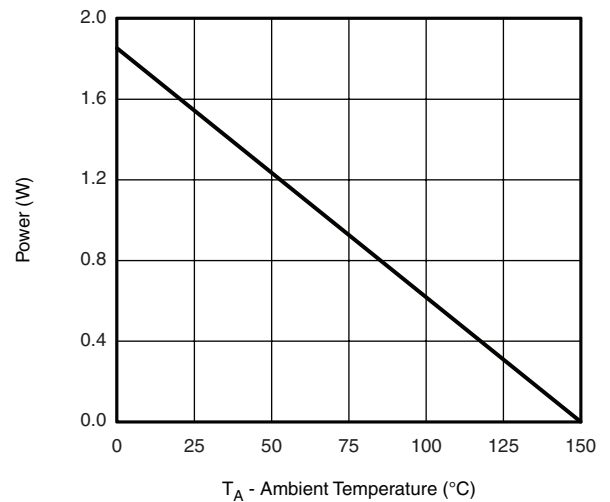
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*

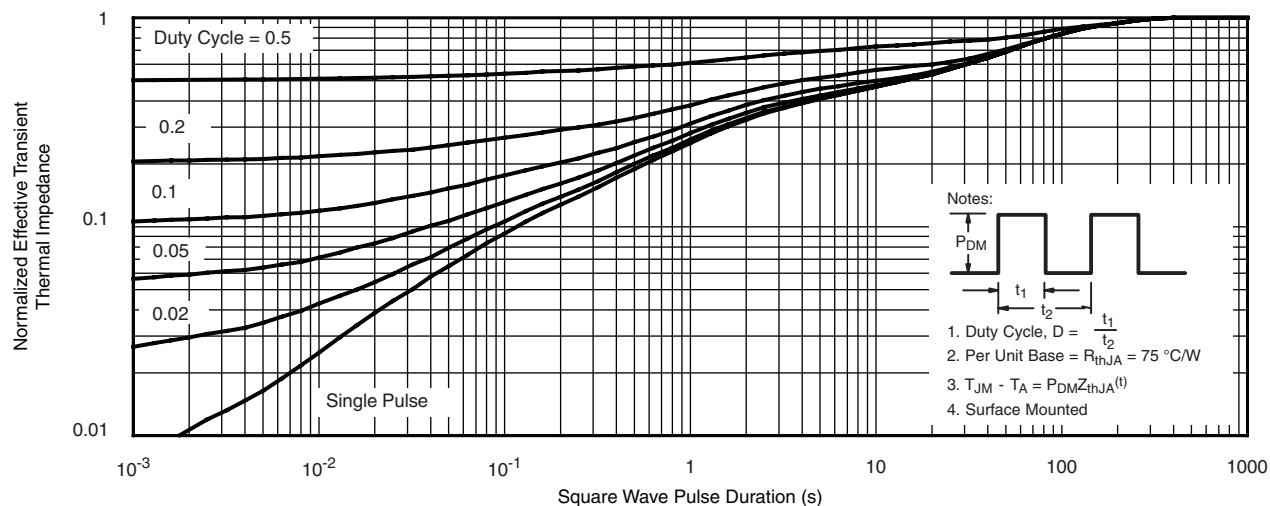
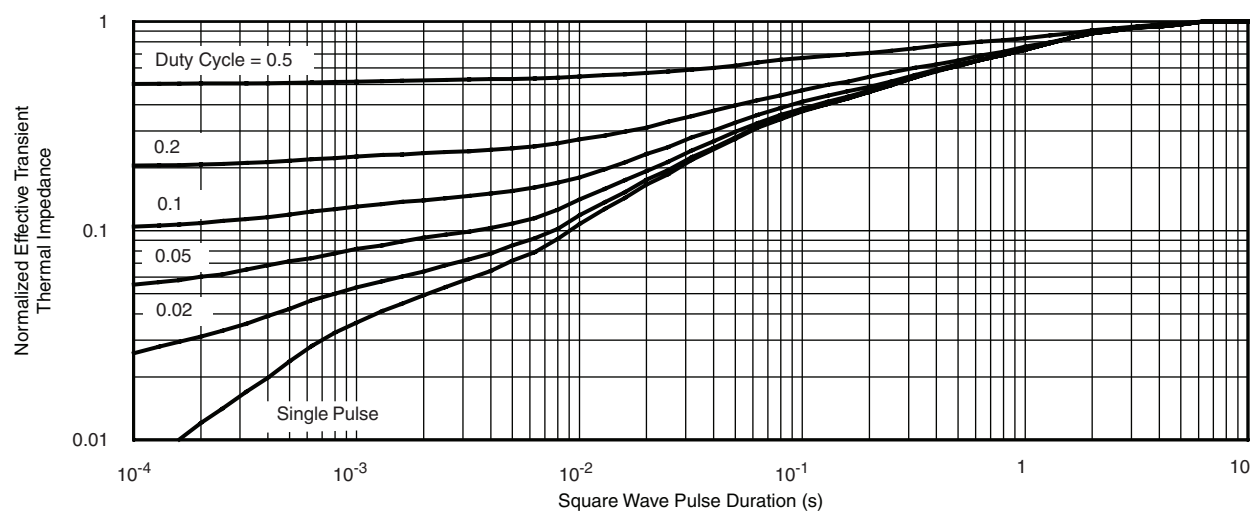


Power Derating, Junction-to-Foot



Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Case**

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